

FS16UM-10

HIGH-SPEED SWITCHING USE

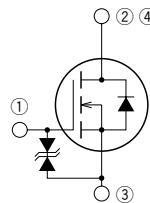
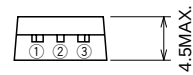
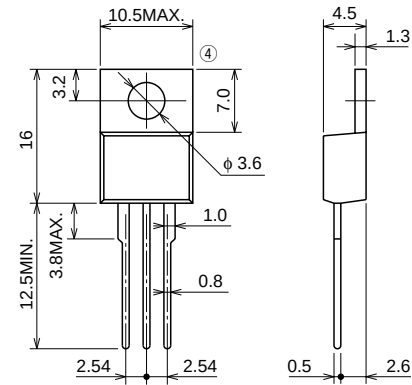
FS16UM-10



- V_{DS} 500V
- $r_{DS(ON)} (MAX)$ 0.56Ω
- I_D 16A

OUTLINE DRAWING

Dimensions in mm



- ① GATE
- ② DRAIN
- ③ SOURCE
- ④ DRAIN

TO-220

APPLICATION

SMPS, DC-DC Converter, battery charger, power supply of printer, copier, HDD, FDD, TV, VCR, personal computer etc.

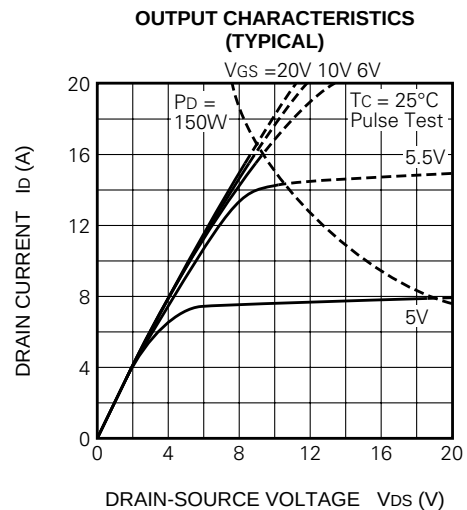
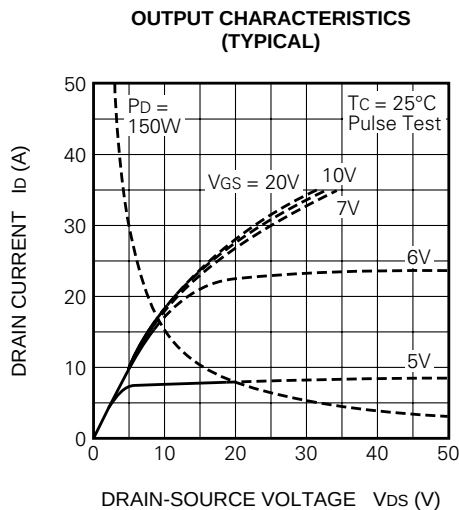
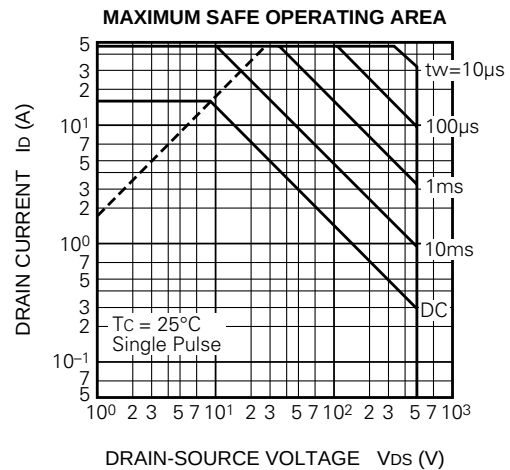
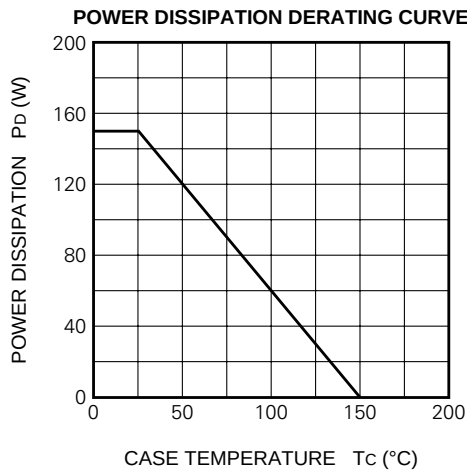
MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	500	V
V_{GS}	Gate-source voltage	$V_{DS} = 0V$	± 30	V
I_D	Drain current		16	A
I_{DM}	Drain current (Pulsed)		48	A
P_D	Maximum power dissipation		150	W
T_{ch}	Channel temperature		$-55 \sim +150$	°C
T_{stg}	Storage temperature		$-55 \sim +150$	°C
—	Weight	Typical value	2.0	g

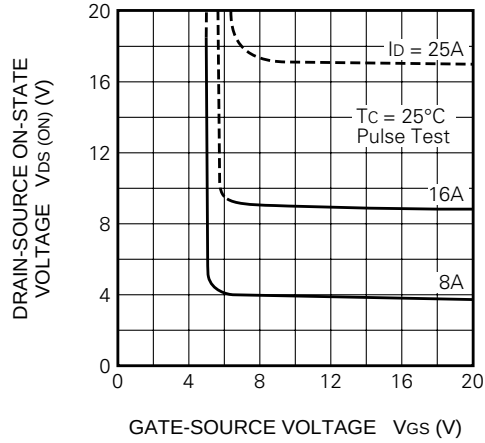
ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	500	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _G = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 500V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2	3	4	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 8A, V _{GS} = 10V	—	0.43	0.56	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 8A, V _{GS} = 10V	—	3.44	4.48	V
y _{fs}	Forward transfer admittance	I _D = 8A, V _{DS} = 10V	6.0	8.0	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	1700	—	pF
C _{oss}	Output capacitance		—	230	—	pF
C _{rss}	Reverse transfer capacitance		—	40	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200V, I _D = 8A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	30	—	ns
t _r	Rise time		—	50	—	ns
t _d (off)	Turn-off delay time		—	170	—	ns
t _f	Fall time		—	60	—	ns
V _{SD}	Source-drain voltage	I _S = 8A, V _{GS} = 0V	—	1.5	2.0	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	0.83	°C/W

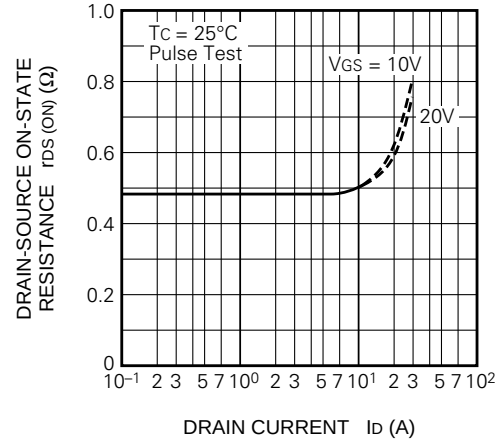
PERFORMANCE CURVES



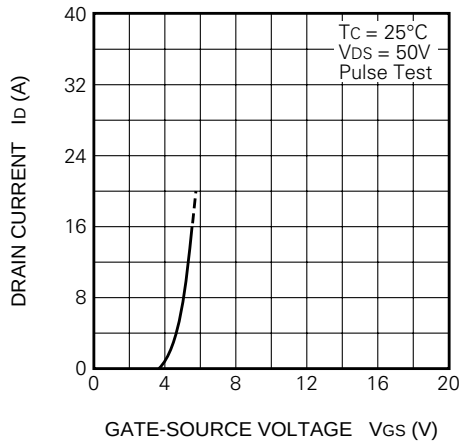
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



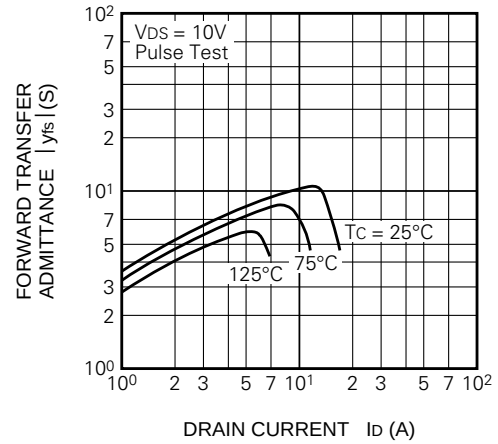
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



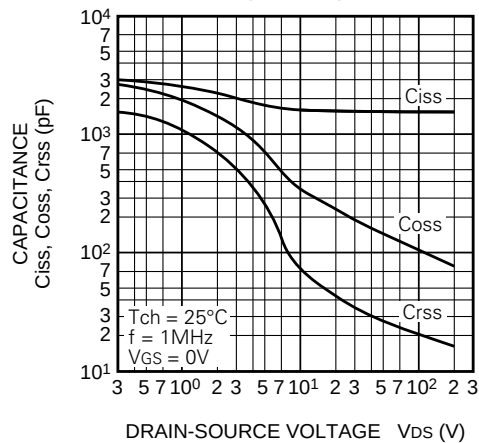
TRANSFER CHARACTERISTICS
(TYPICAL)



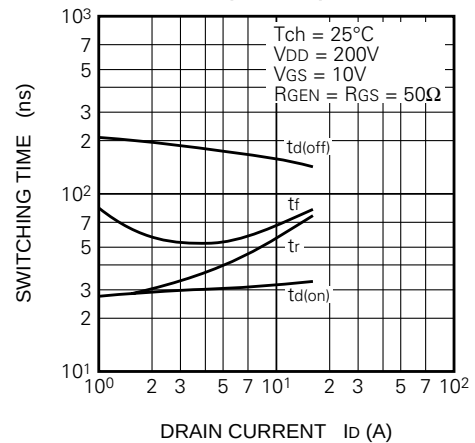
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



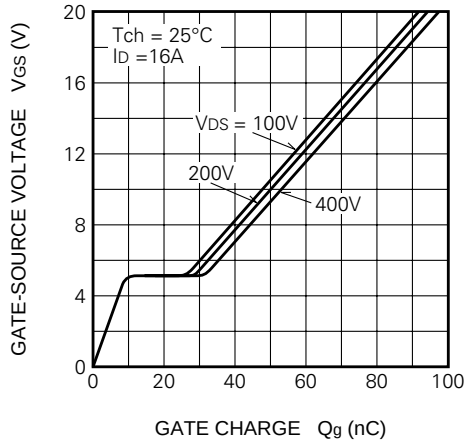
CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



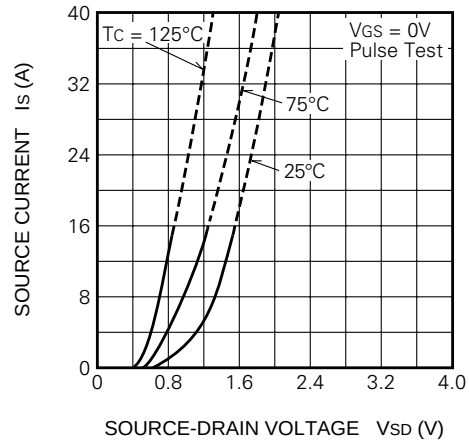
SWITCHING CHARACTERISTICS
(TYPICAL)



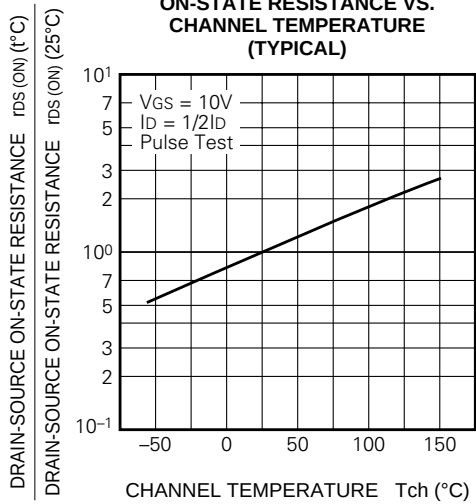
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



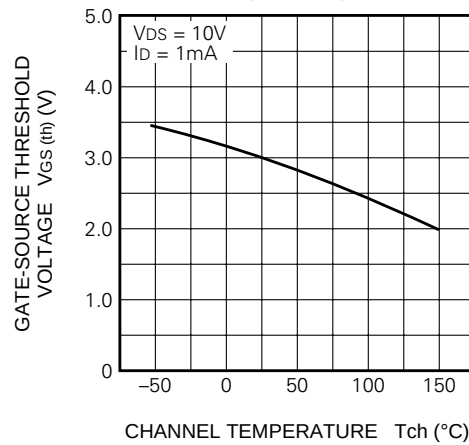
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



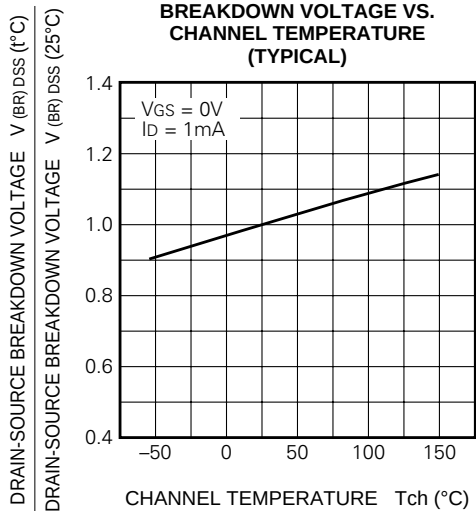
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

